

Silicon NPN Power Transistors

2SD882

DESCRIPTION

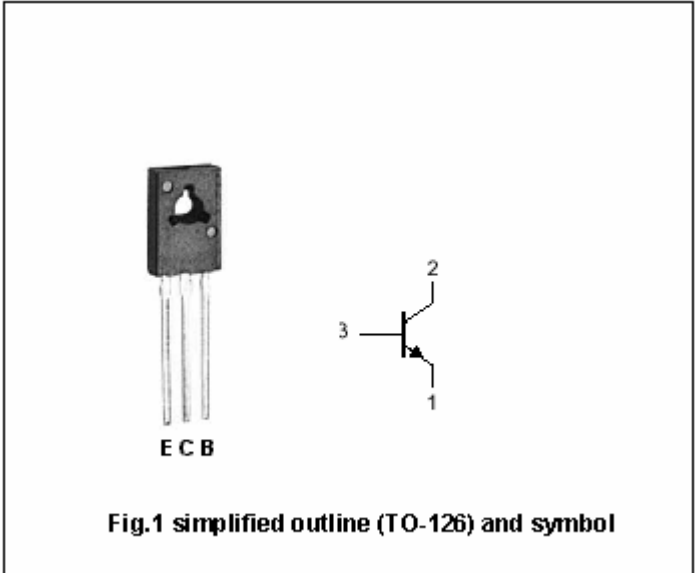
- With TO-126 package
- Complement to type 2SB772

APPLICATIONS

- Audio amplifier
- Voltage regulator
- DC-DC converter
- Relay driver

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	40	V
V _{CEO}	Collector-emitter voltage	Open base	30	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		3	A
I _{CM}	Collector current-peak		7	A
P _D	Total power dissipation	T _a =25℃	1	W
		T _C =25℃	10	
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	30			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2.0A ; I_B=0.2A$			0.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2.0A ; I_B=0.2A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=30V ; I_E=0$			1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=3V ; I_C=0$			1	μA
h_{FE-1}	DC current gain	$I_C=20mA ; V_{CE}=2V$	30			
h_{FE-2}	DC current gain	$I_C=1A ; V_{CE}=2V$	60		400	
f_T	Transition frequency	$I_C=0.1A ; V_{CE}=5V$		90		MHz
C_{OB}	Collector output capacitance	$f=1MHz ; V_{CB}=10V$		45		pF

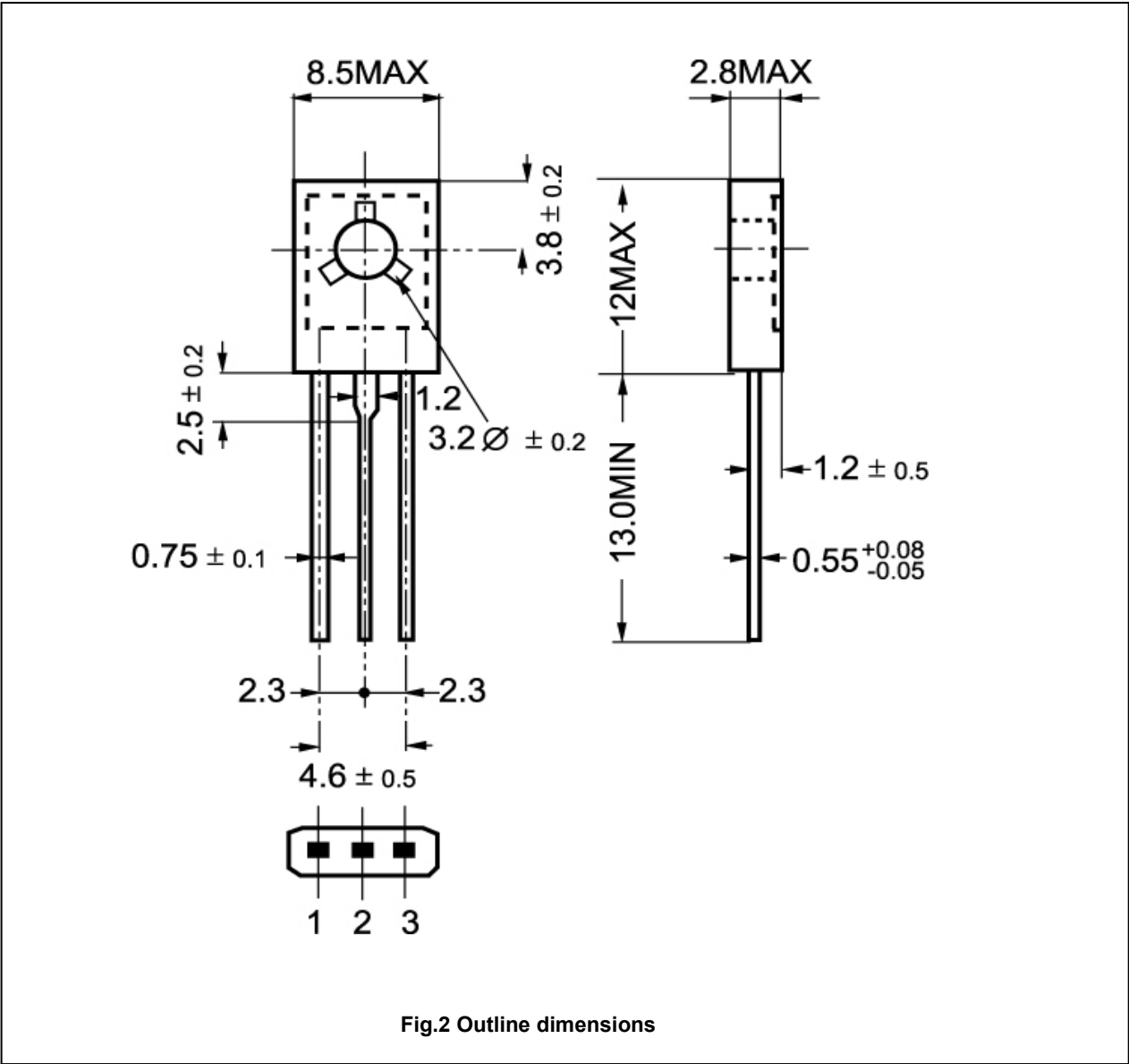
◆ h_{FE-2} Classifications

R	Q	P	E
60-120	100-200	160-320	200-400

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PACKAGE OUTLINE



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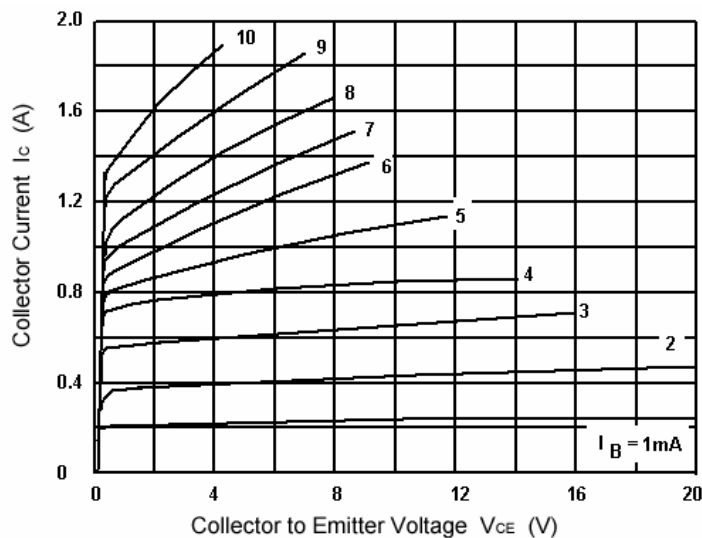


Fig.3 Static Characteristic

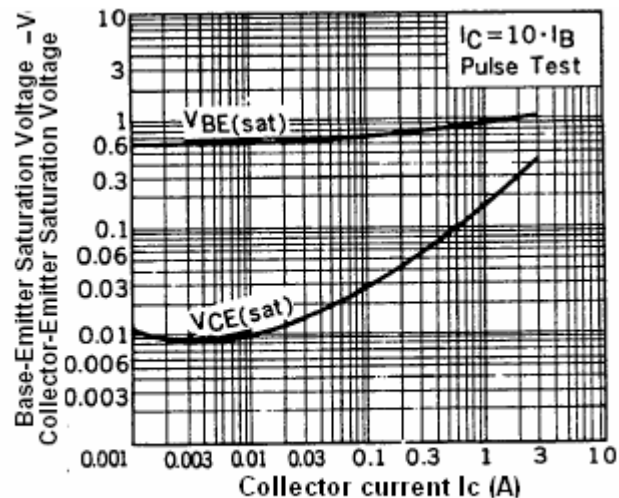
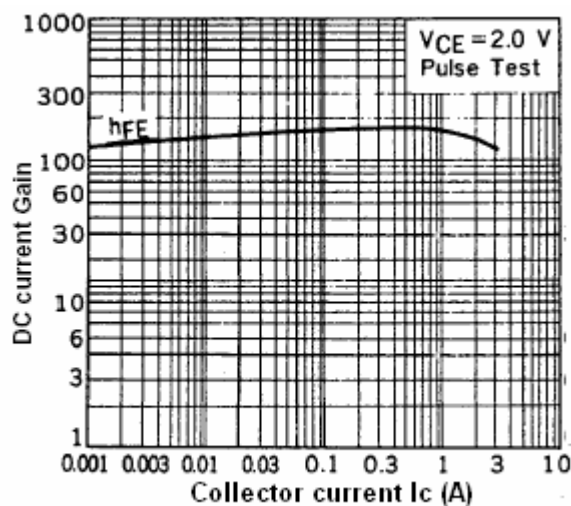
Fig.4 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

Fig.5 DC current Gain

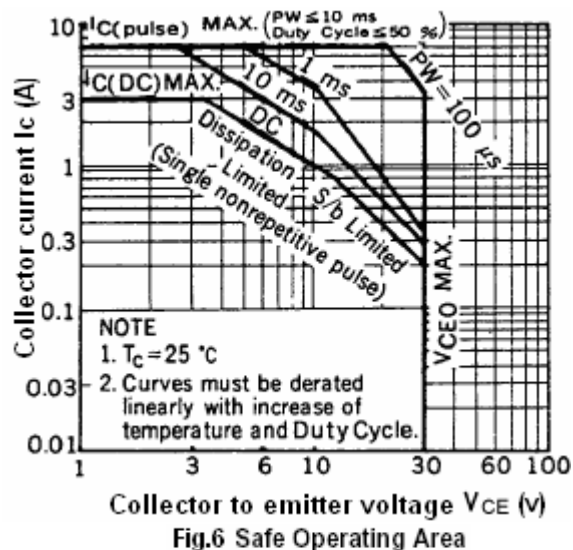


Fig.6 Safe Operating Area